Wuxi Unigroup Microelectronics CO.,LTD.

85V N-Channel Trench MOSFET(Preliminary)

General Description

- Trench Power Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching Applications

Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

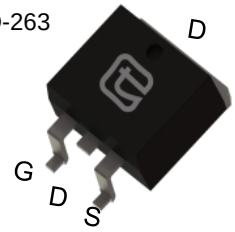
Product Summary

V_{DS}	85V
I_D (at V_{GS}=10V)	85A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 9mΩ

100% UIS Tested

RoHS

TO-263



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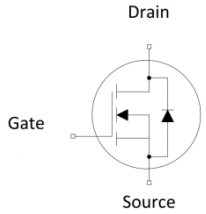


Device	Package	Form	Marking
TTB85N08A	TO-263	Tape & Reel	85N08A
TTP85N08A	TO-220	Tube	85N08A

Absolute Maximum Ratings (T_A =25ºC unless otherwise noted)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	85	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B]	T_C = 25ºC	I_D	85	A
	T_C = 100ºC		55	
Pulsed Drain Current [A]		I_{DM}	255	A
Avalanche Current [A]		I_{AS}	40	A
Single Pulse Avalanche Energy L =0.3mH [A]		E_{AS}	240	mJ
Power Dissipation [C]	T_C = 25ºC	P_D	160	W
	T_C = 100ºC		78	W
Operating Junction and Storage Temperature Range		T_J, T_{SGT}	-55 to 175	ºC

Thermal Resistance

Parameter		Symbol	Maximum	Units
Thermal Resistance, Junction-to-Case	Steady-State	R_{thJC}	0.95	ºC/W
Thermal Resistance, Junction-to-Ambient	Steady-State	R_{thJA}	100	

Electrical Characteristics(T_J =25ºC unless otherwise noted)

Symbol	Parameter	Conditions		Value			Units
				Min	Typ	Max	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D = 250μA,V_{GS} = 0V		85	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 85V, V_{GS} = 0V	T_J =25ºC	--	--	1	μA
			T_J =100ºC	--	--	25	
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} =±20V		--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA		2	3	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 30A		--	8.4	9	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 20A		30	--	--	S
V_{SD}	Diode Forward Voltage	I_S = 20A, V_{GS} = 0V		--	--	1	V
I_S	Maximum Body-Diode Continuous Current [B]			--	--	85	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS} =0V, V_{DS} = 40V, f =1MH_Z		--	5400	--	pF
C_{oss}	Output Capacitance			--	245	--	
C_{rss}	Reverse Transfer Capacitance			--	204	--	
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS} =10V,V_{DS} = 40V, I_D = 20A		--	92	--	nC
Q_{gs}	Gate Source Charge			--	27	--	
Q_{gd}	Gate Drain Charge			--	21	--	
$t_{D(on)}$	Turn-On Delay Time	V_{GS} =10V,V_{DS} = 40V, I_D =20A, R_G =2.5Ω		--	24	--	ns
t_r	Turn-On Rise Time			--	19	--	
$T_{D(off)}$	Turn-Off Delay Time			--	70	--	
t_f	Turn-Off Fall Time			--	30	--	
t_{rr}	Body Diode Reverse Recovery Time	I_F =20A, di/dt =100A/μs		--	37	--	ns
Q_{rr}	Body Diode Reverse Recovery Charge			--	58	--	nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)}$ =175ºC, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

Typical Characteristics T_J = 25ºC, unless otherwise noted

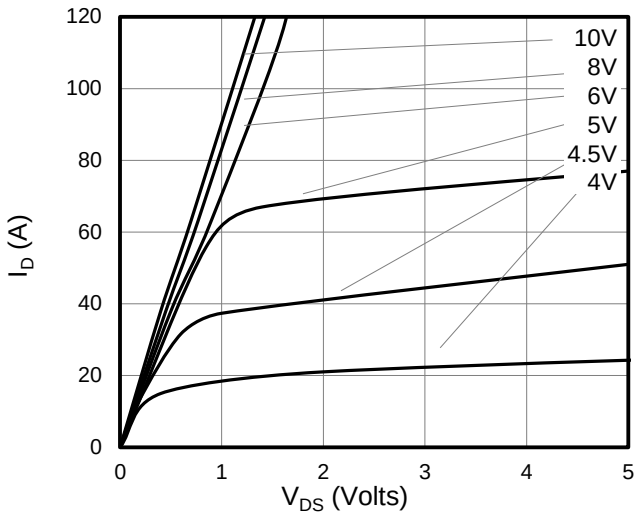


Figure 1: On-Region Characteristics

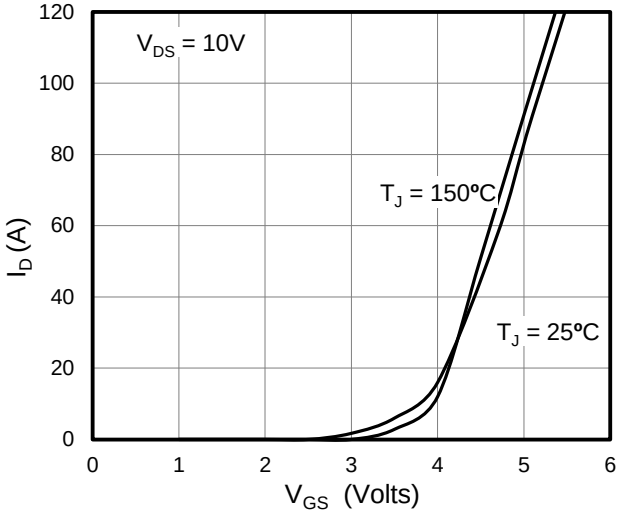


Figure 2: Transfer Characteristics

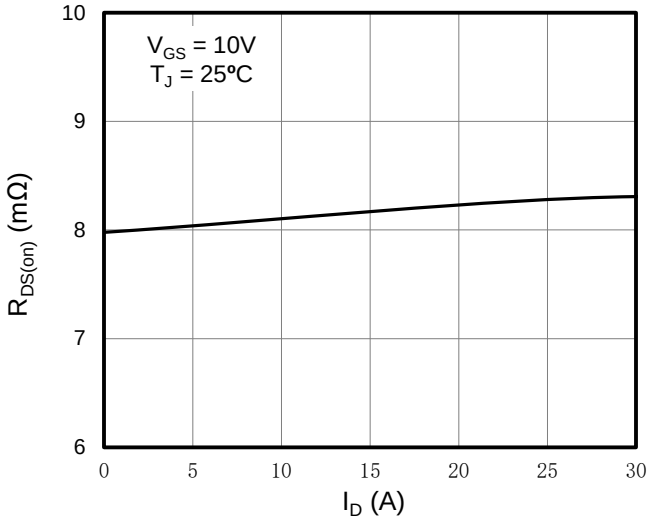


Figure 3: On-Resistance vs. Drain Current

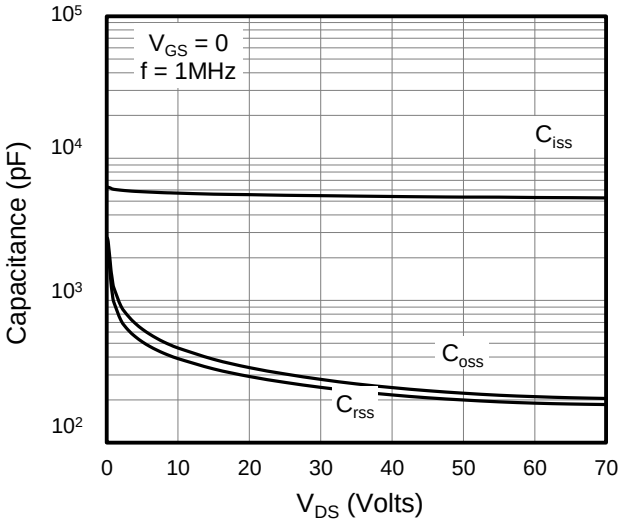


Figure 4: Capacitance Characteristics

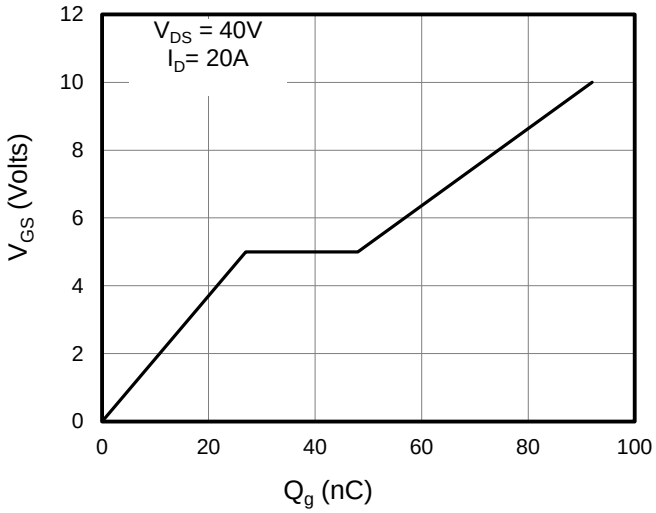


Figure 5: Gate Charge Characteristics

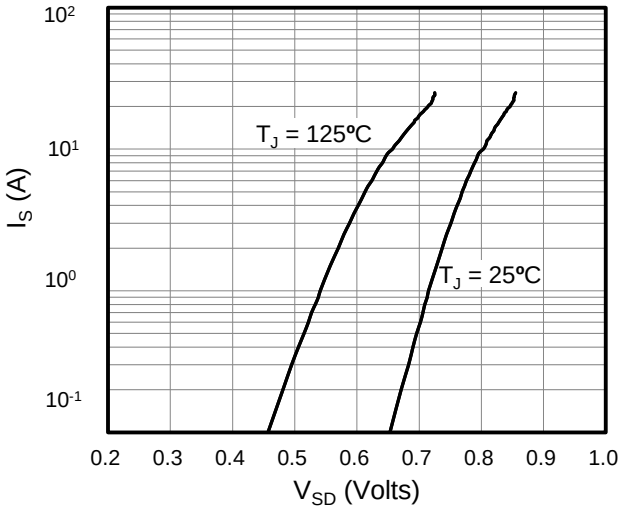


Figure 6: Body Diode Forward Voltage

Typical Characteristics T_J = 25ºC, unless otherwise noted

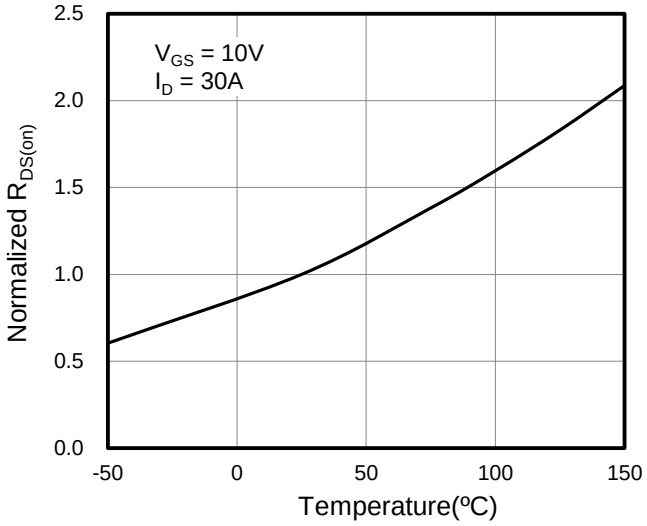


Figure 7: On-Resistance vs. Junction Temperature

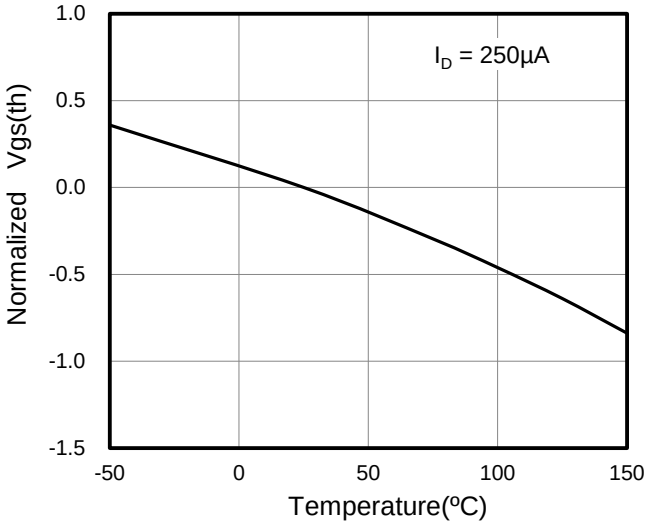


Figure 8: Vgs(th) vs. Junction Temperature

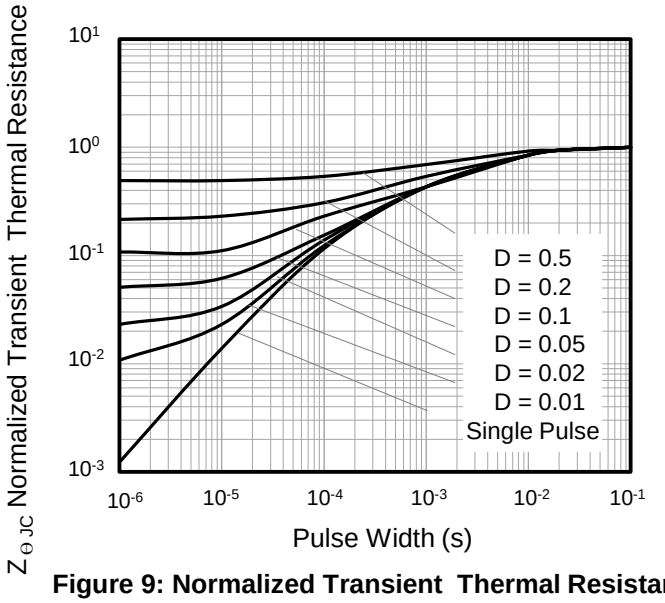


Figure 9: Normalized Transient Thermal Resistance

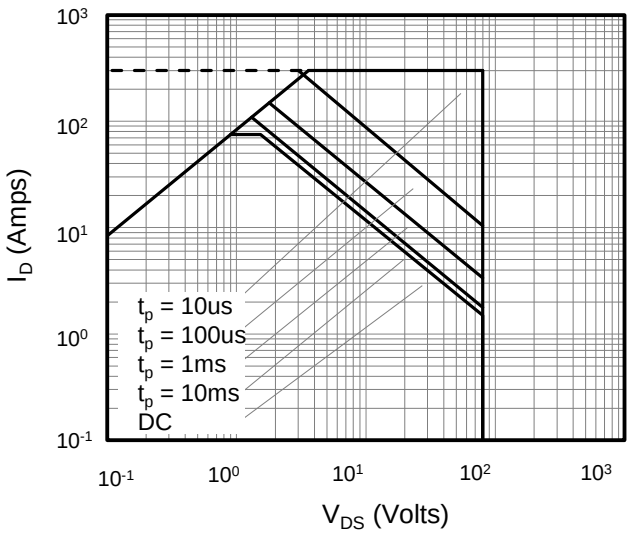


Figure 10: Safe Operating Area

Figure A：Gate Charge Test Circuit and Waveform

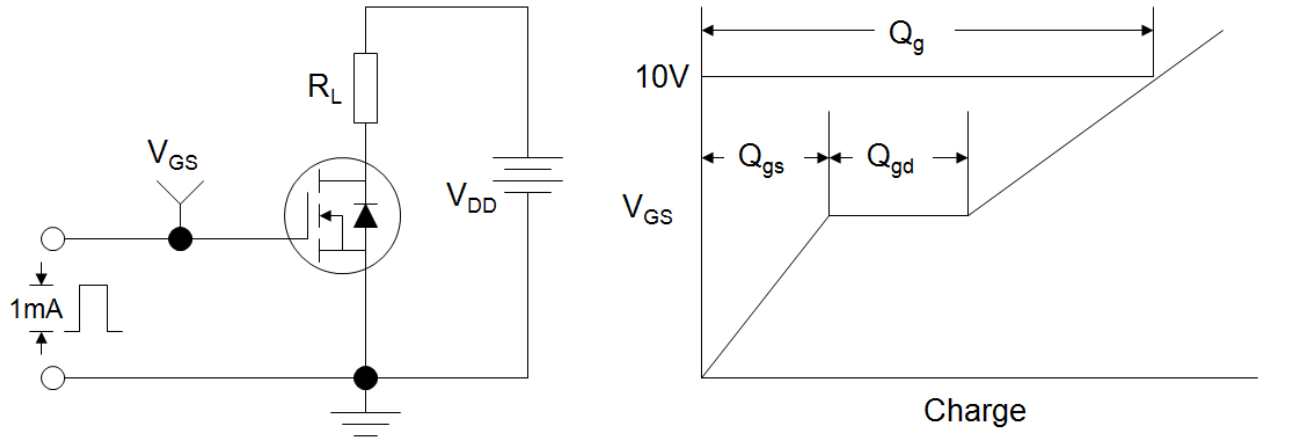


Figure B：Resistive Switching Test Circuit and Waveform

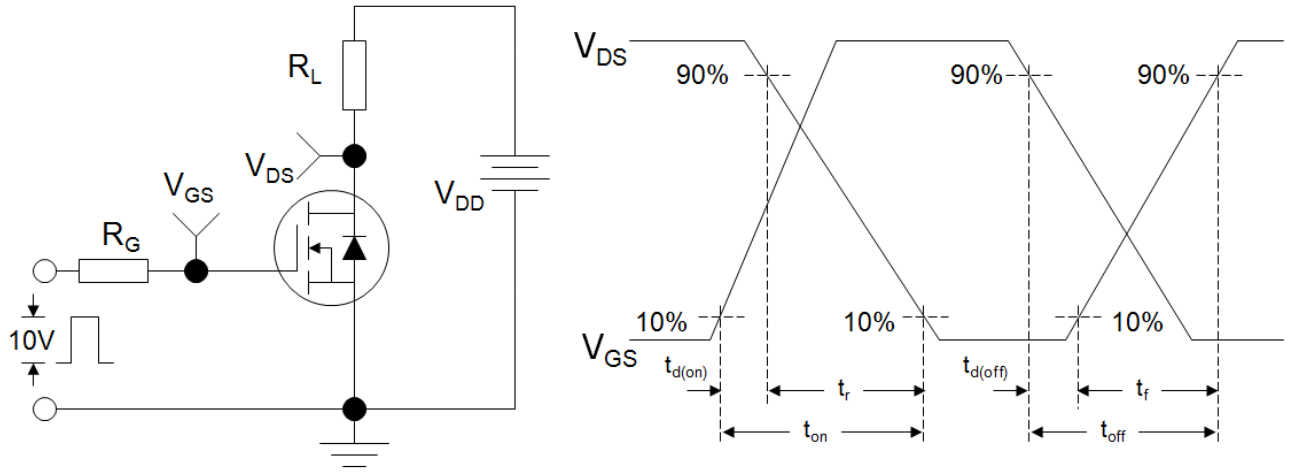
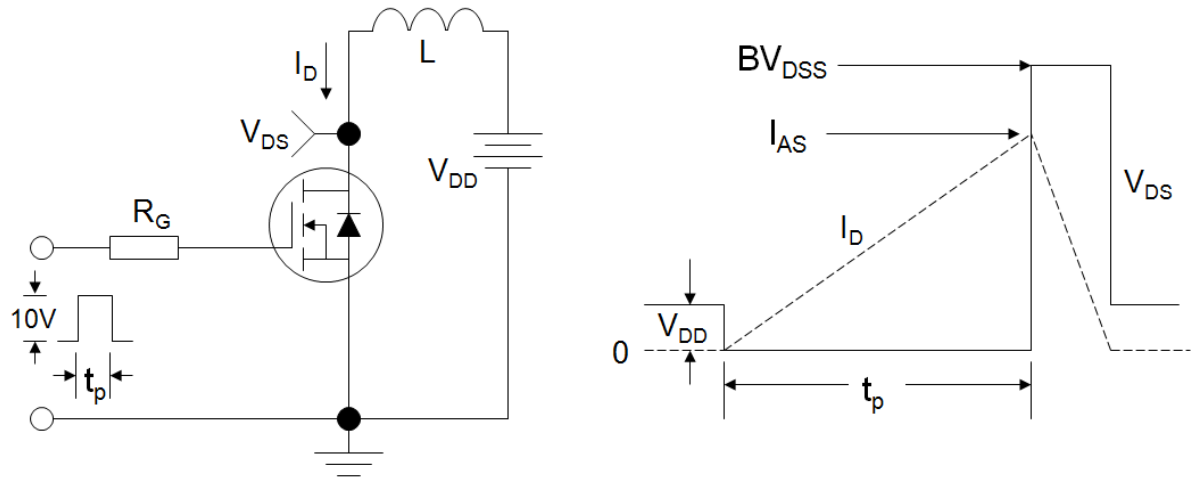


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



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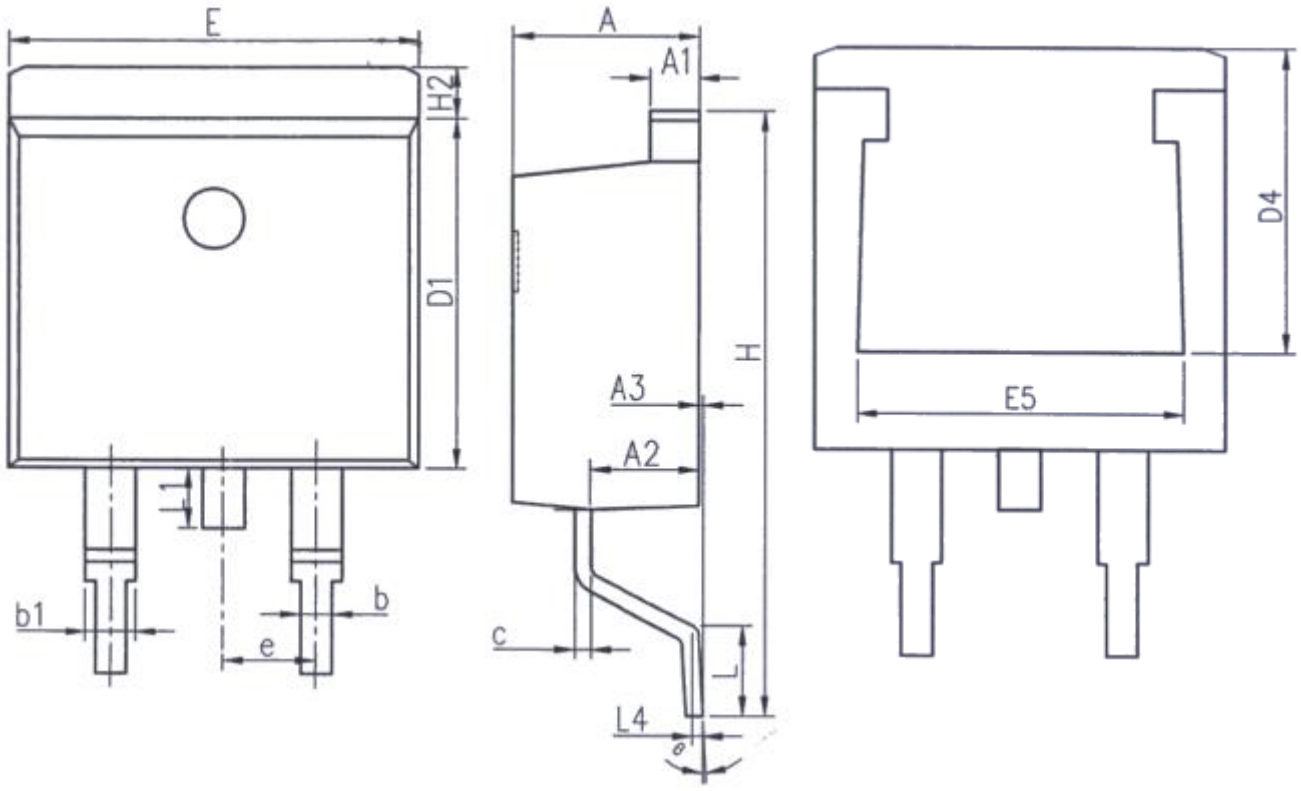

Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.49	2.89
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.50	8.90
D4	6.60	-

Unit: mm		
Symbol	Min.	Max.
E	9.86	10.36
E5	7.06	-
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.60
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°

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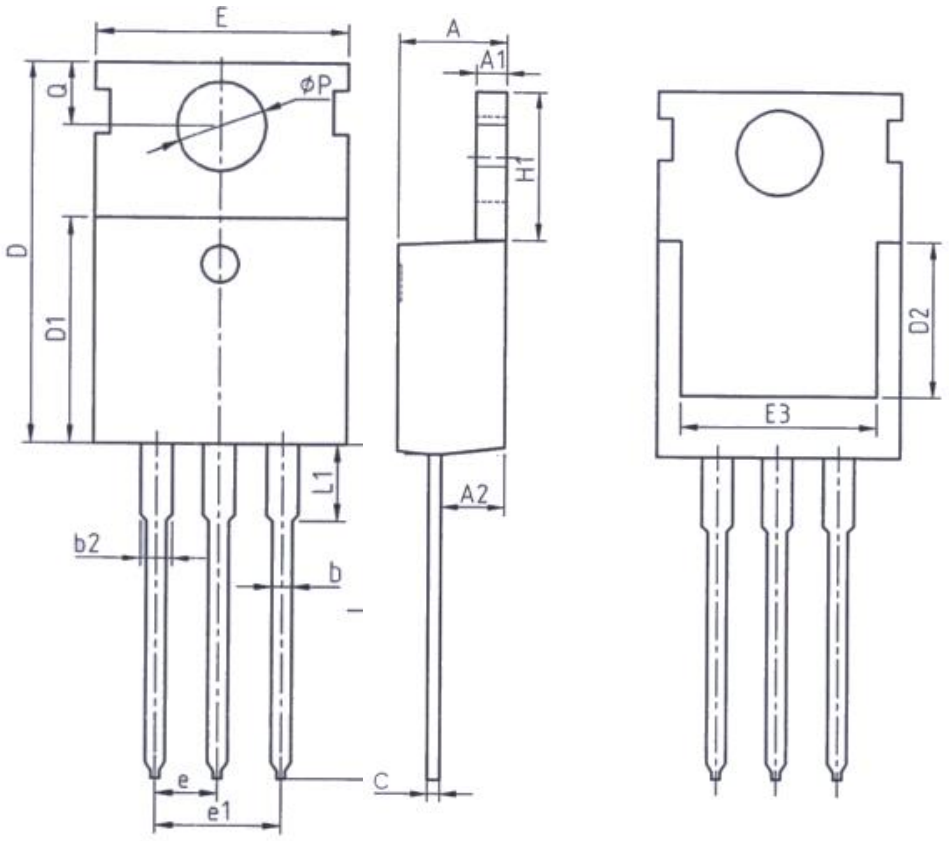

Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	–

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	–
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	–	3.40
P	3.40	3.80
Q	2.60	3.00

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